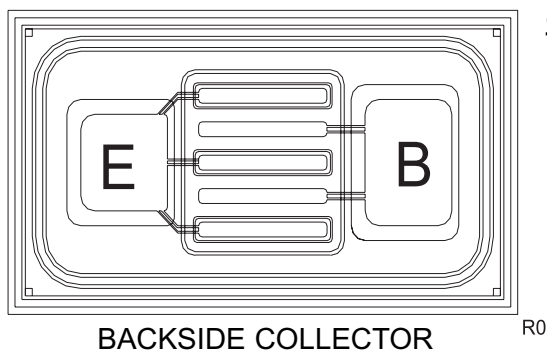


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	12 x 20 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.6 X 3.6 MILS
Emitter Bonding Pad Area	3.6 X 3.6 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



GROSS DIER PER 4 INCH WAFER

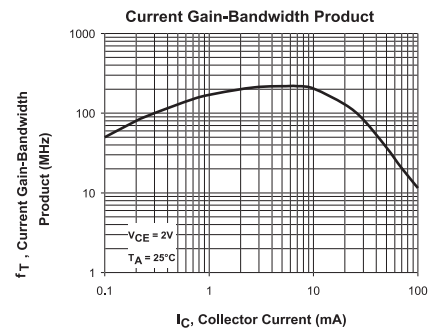
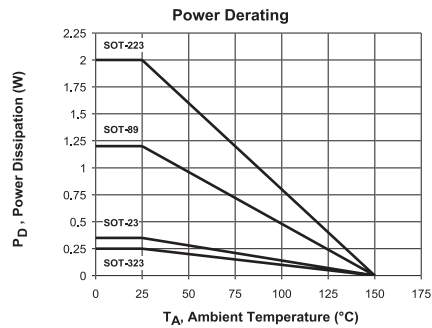
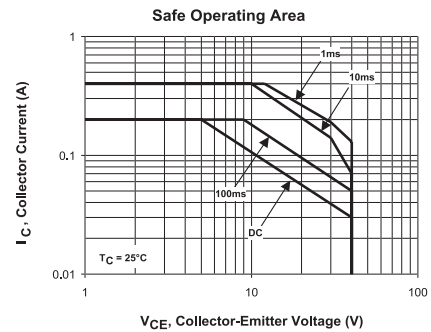
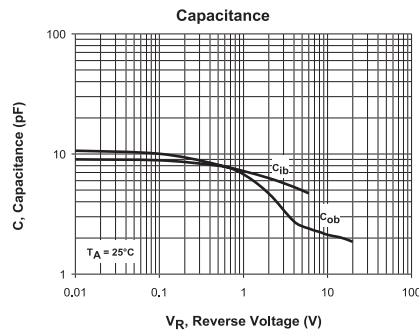
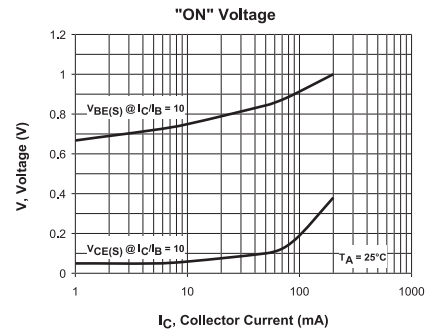
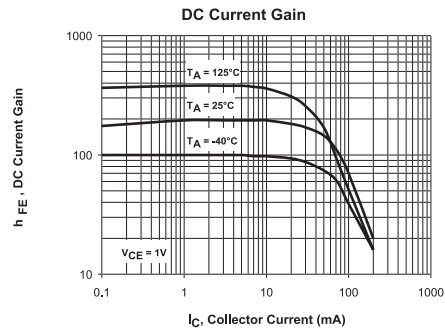
47,150

PRINCIPAL DEVICE TYPES

2N3906
CMKT3906
CMLT3906E
CMPT3906
CMST3906
CXT3906
CZT3906

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